

Pb Free Product

Description

The RSTB301G is designed to provide a high efficiency synchronous buck power stage with optimal layout and board space utilization. It includes two specialized MOSFETs in a dual Power DFN5x6 package. The Q1 "High Side" MOSFET is designed to minimize switching losses. The Q2 "Low Side" MOSFET uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge.

General Features

Q1 "High Side" MOSFET

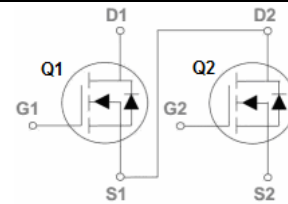
- $V_{DS} = 30V, I_D = 20A$
 $R_{DS(ON)} < 8.5m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Q2 "Low Side" MOSFET

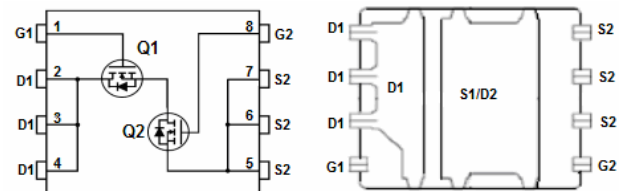
- $V_{DS} = 30V, I_D = 35A$
 $R_{DS(ON)} < 7m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = 4.5V$

Application

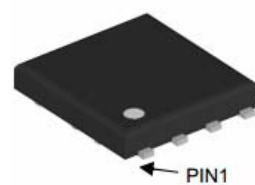
- Compact DC/DC converter applications



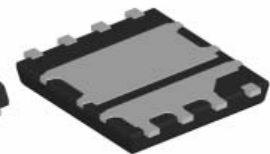
Schematic Diagram



pin assignment



Top View



Bottom View

100% UIS TESTED!
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
RSTB301G	RSTB301G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Q1	Q2	Unit
Drain-Source Voltage	V_{DS}	30	30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Drain Current-Continuous (Note 2)	I_D	20	35	A
		14.1	24.7	
Drain Current -Pulsed (Note 1)	I_{DM}	80	120	A
Power Dissipation	P_D	20	40	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ C$

Thermal Characteristic

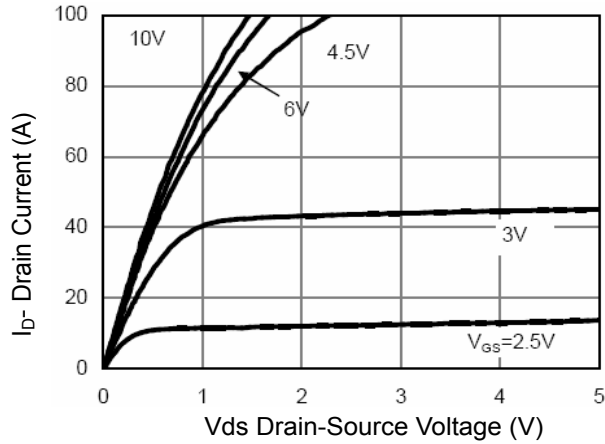
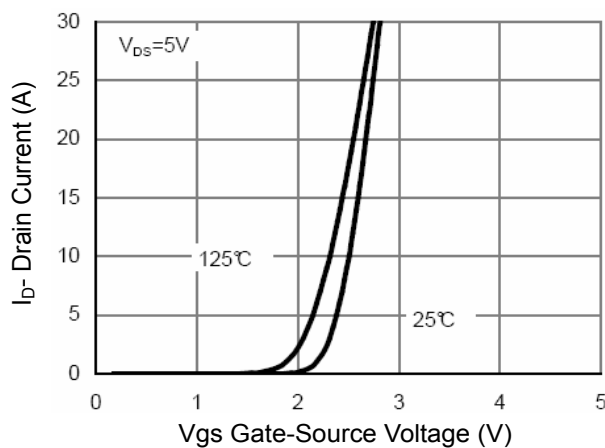
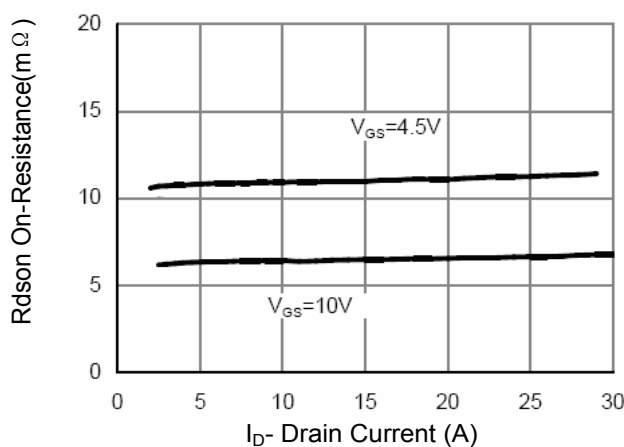
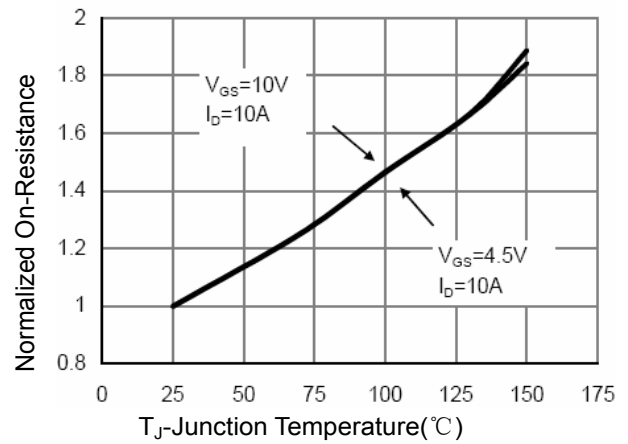
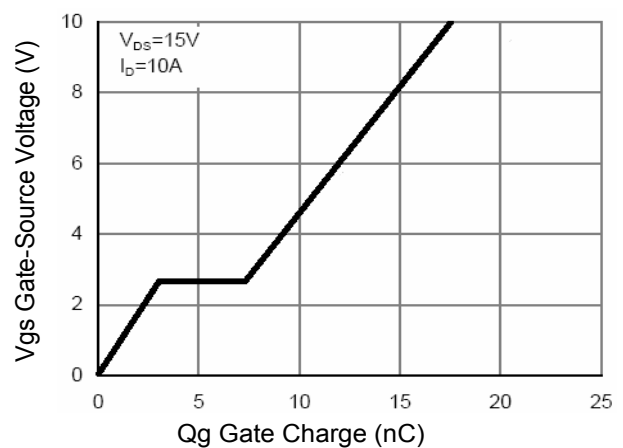
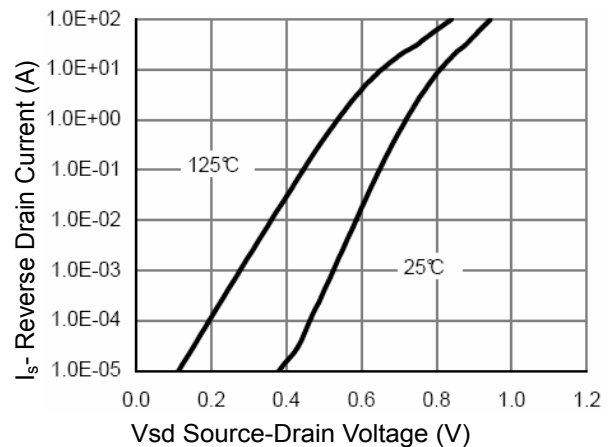
Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case (Note 2) (Q1)	$R_{\theta JC}$	6	6.3	$^\circ C/W$
Thermal Resistance, Junction-to-Case (Note 2) (Q2)	$R_{\theta JC}$	2.9	3.1	$^\circ C/W$

Q1 Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	6.9	8.5	mΩ
		V _{GS} =4.5V, I _D =10A	-	10.8	14	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10A	26	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	1210	-	PF
Output Capacitance	C _{oss}		-	160	-	PF
Reverse Transfer Capacitance	C _{rss}		-	105	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =0.75Ω V _{GS} =10V, R _G =3Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	12	-	nS
Turn-Off Delay Time	t _{d(off)}		-	19	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =10A, V _{GS} =10V	-	17.5		nC
Gate-Source Charge	Q _{gs}		-	3		nC
Gate-Drain Charge	Q _{gd}		-	4.1		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	20	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =10A	-	19	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs ^(Note3)	-	10	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25Ω

Q1 Typical Electrical and Thermal Characteristics (Curves)

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

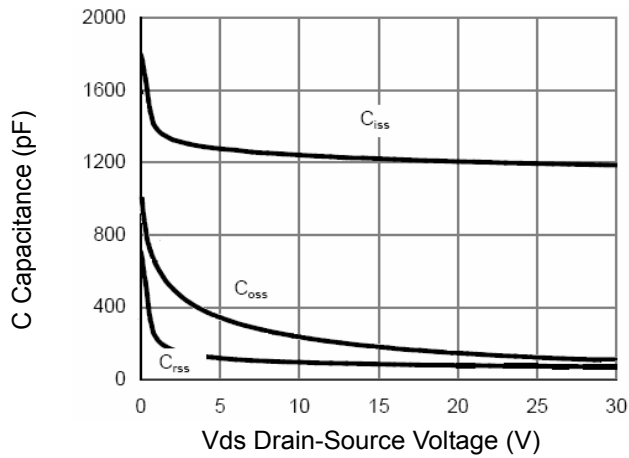


Figure 7 Capacitance vs Vds

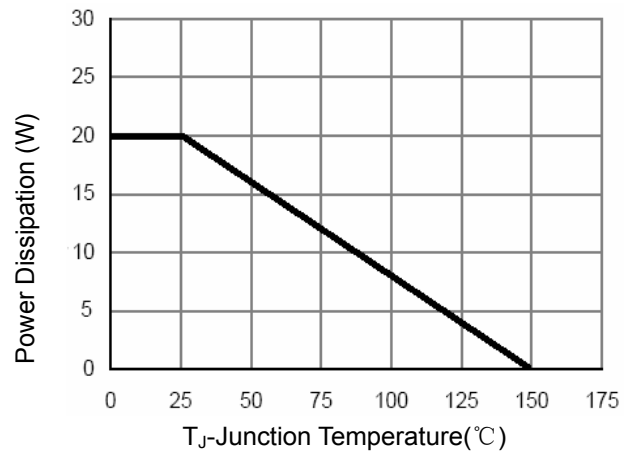


Figure 9 Power De-rating

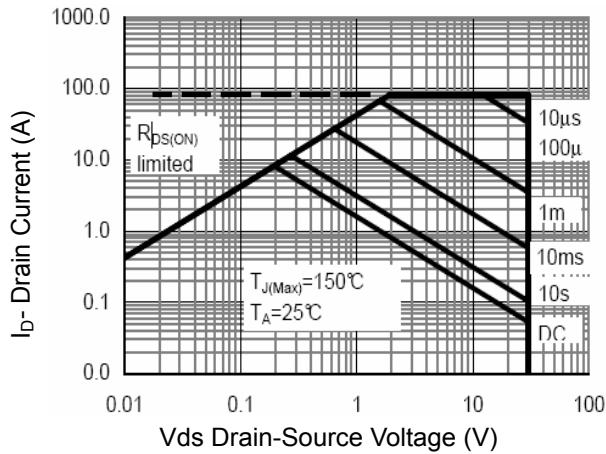


Figure 8 Safe Operation Area

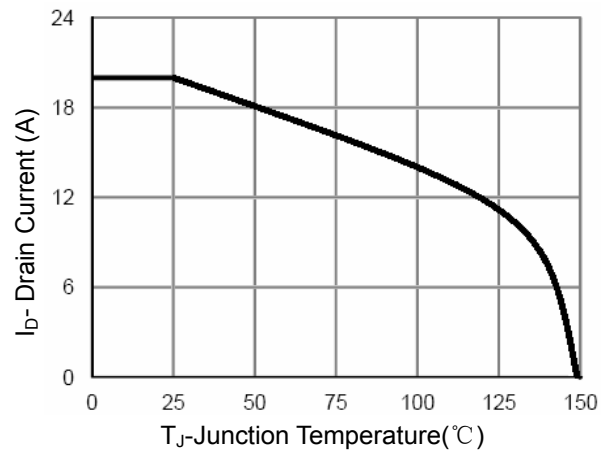


Figure 10 ID Current De-rating

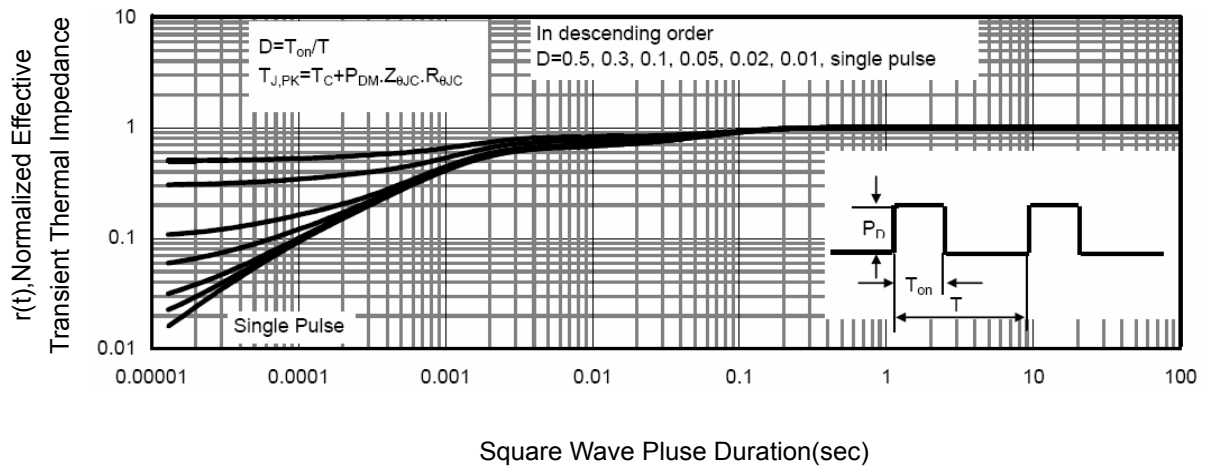


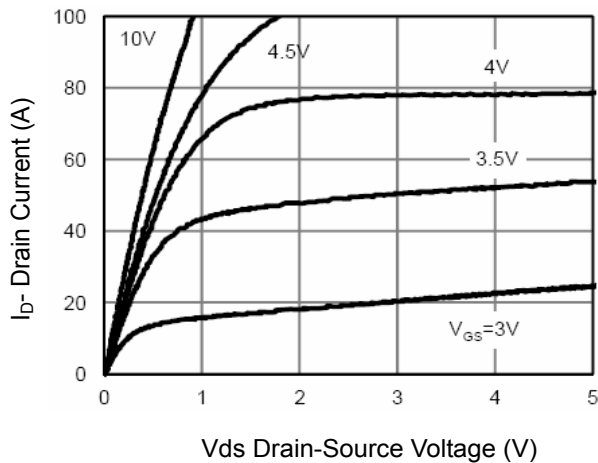
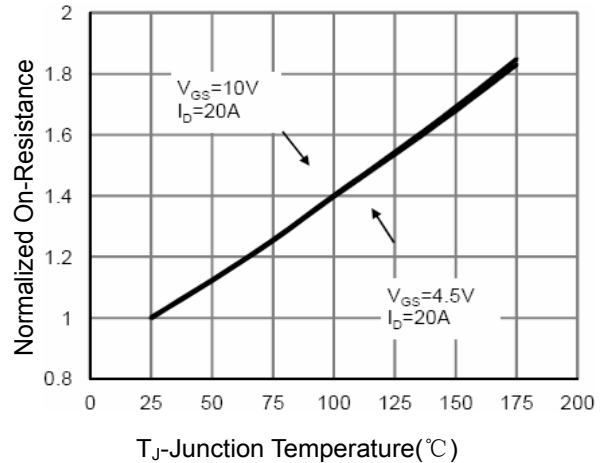
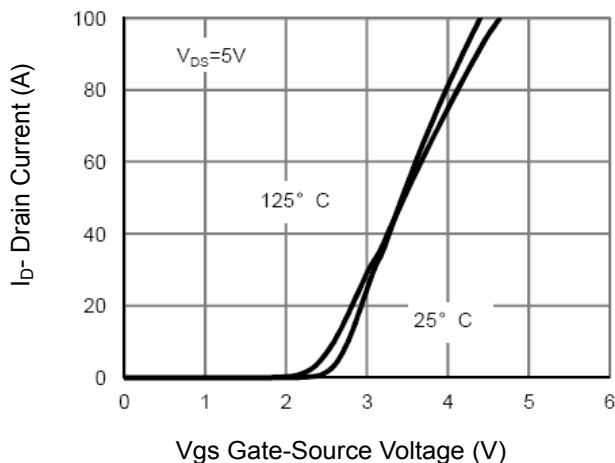
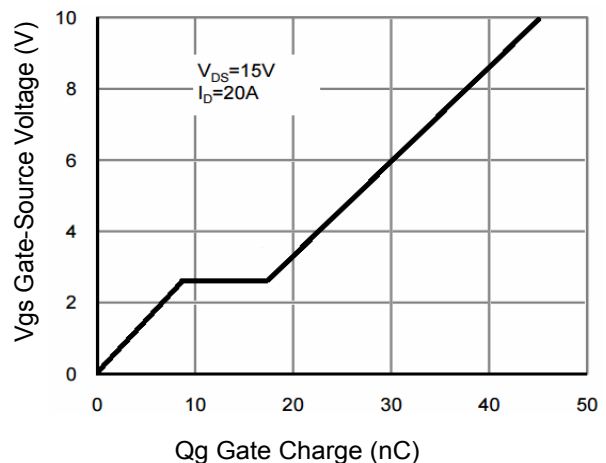
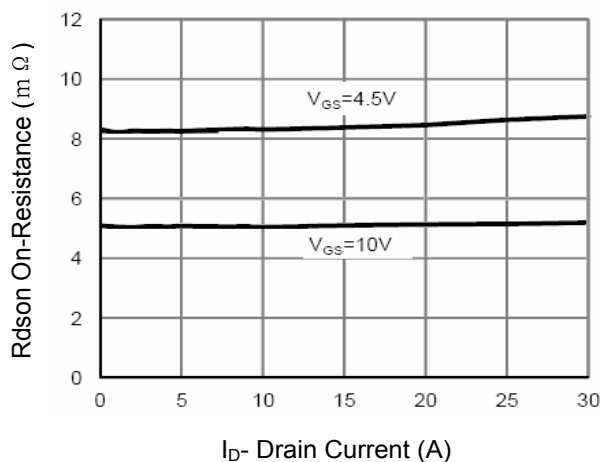
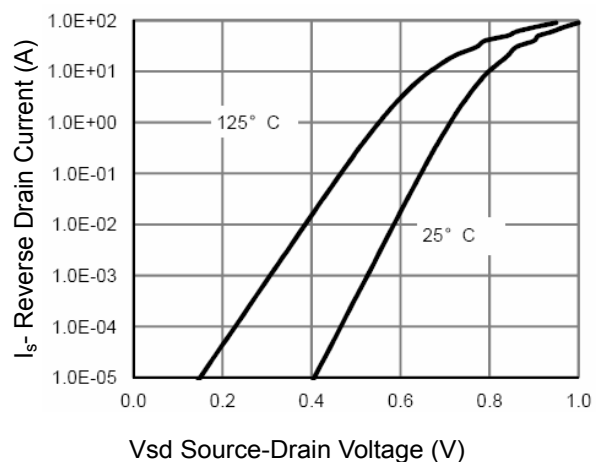
Figure 11 Normalized Maximum Transient Thermal Impedance

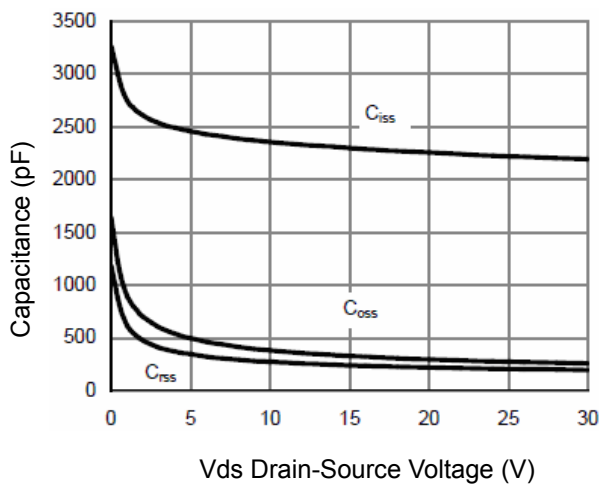
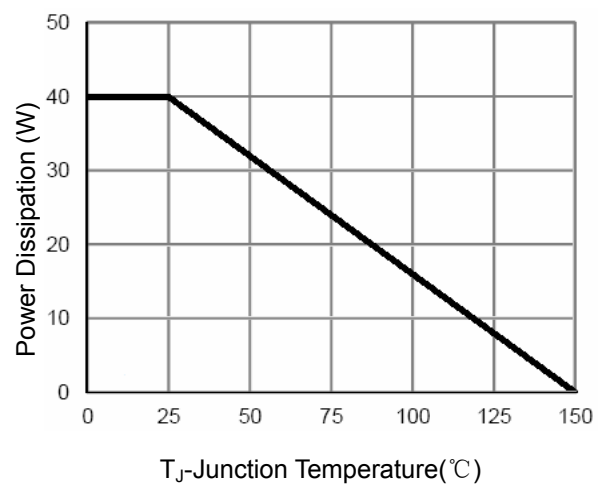
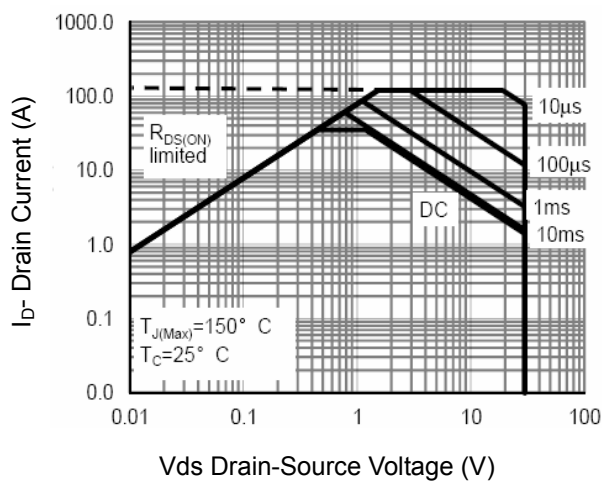
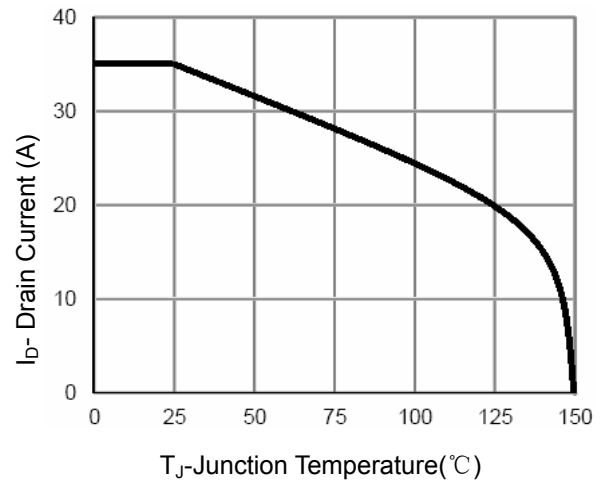
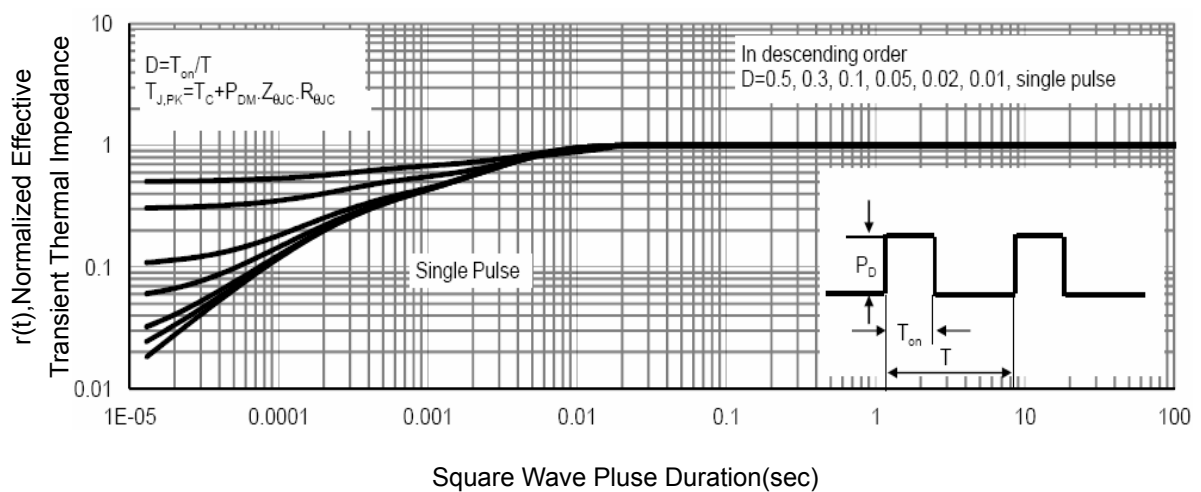
Q2 Electrical Characteristics (TC=25°C unless otherwise noted)

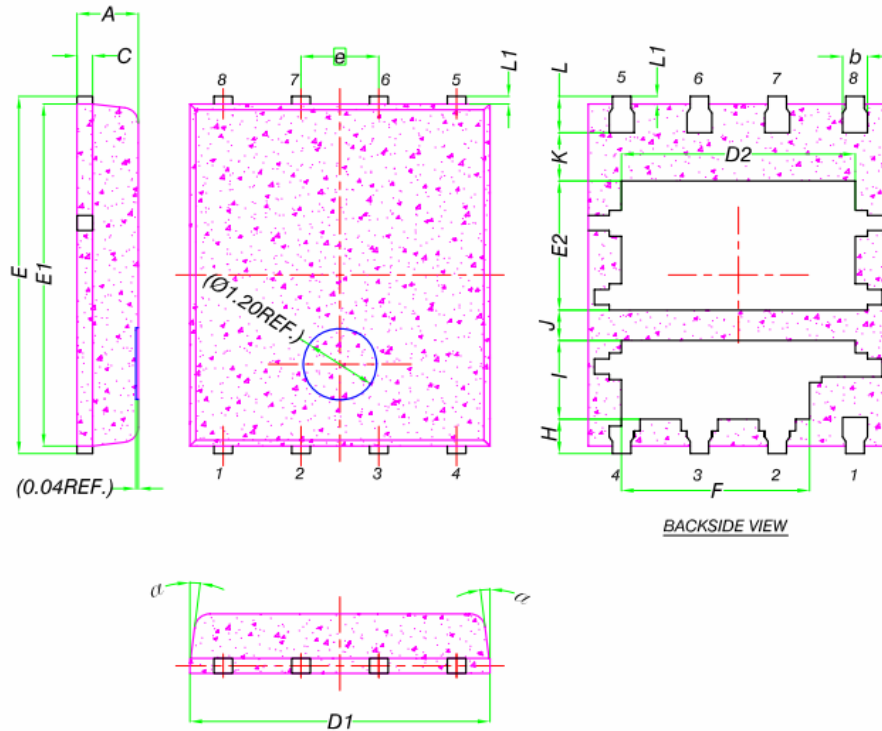
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	-	5.1	7.0	mΩ
		V _{GS} =4.5V, I _D =10A	-	8.3	12.0	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =12A	30	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2330	-	PF
Output Capacitance	C _{oss}		-	460	-	PF
Reverse Transfer Capacitance	C _{rss}		-	230	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =12A V _{GS} =10V, R _{GEN} =6Ω	-	18	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =12A, V _{GS} =10V	-	45	-	nC
Gate-Source Charge	Q _{gs}		-	9.4	-	nC
Gate-Drain Charge	Q _{gd}		-	7.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =12A	-	0.85	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	35	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 12A	-	-	47	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs(Note3)	-	-	25	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$

Q2 Typical Electrical and Thermal Characteristics (Curves)

Figure 1 Output Characteristics

Figure 4 Rdson-Junction Temperature

Figure 2 Transfer Characteristics

Figure 5 Gate Charge

Figure 3 Rdson- Drain Current

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information


DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.02	2.17	2.32
[e]	1.27 BSC		
F	2.87	3.07	3.22
H	0.48	0.58	0.68
I	1.22	1.32	1.42
J	0.40	0.50	0.60
K	0.50	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

